



《风光欣》技术资料

8050

NPN EPITAXIAL SILICON TRANSISTOR

*Features

High h_{FE} : 160~320

Low Collector Saturation Voltage

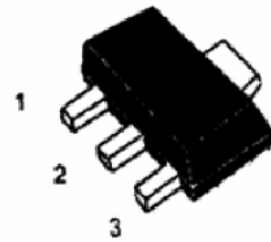
$V_{CE(sat)} = 0.5V(\text{Max.})$ $I_C = 500mA, I_B = 20mA$

Complementary Pair With 8550

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Collector Dissipation	P_C	225	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-89



1,Base 2,Collector 3, Emitter

ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 500 \mu A, I_E = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1mA, I_B = 0$	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 50 \mu A, I_C = 0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			500	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			500	nA
DC Current Gain	h_{FE}	$V_{CE} = 1V, I_C = 50mA$	160		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 20mA$			0.5	V
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 10mA$		120		MHz
Collector Output Capacitance	C_{ob}	$f = 1MHz, V_{CB} = 10V, I_E = 0$		9		pF